

HM6118B 20V, 1A High Speed LDO

General Description

The HM6118B series are the low noise LDO with enable function, the output operates from 0.8V to 5.0V by 0.1V/step. The characteristics are low noise and good PSRR and low dropout voltage, make this device ideal for portable consumer applications.

The HM6118B series can operate with up to 20V input.

The Devices are available in SOT223 ,SOT89-3,ESOP8, TO252-2L, DFN6 packages

Features

- Operating Input Voltage Range:2.7V~20V
- Max Output Current: 1A
- Output Voltage Accuracy: ±2%
- Adjustable Output Voltage Option V_{FB}=0.6V
- Fixed Output Voltage Version : 0.8V~5.5V
- Standby Current: 100uA (Typ.)
- High Ripple Rejection: 80dB at 1kHz
- Low Dropout: 0.6V (Typ.) at 1A @ Vout ≥2V

Applications

- Consumer and Industrial Equipment Point of Regulation.
- Switching Power Supply Post Regulation
- Battery Chargers
- Hard Drive Controllers

Device Information

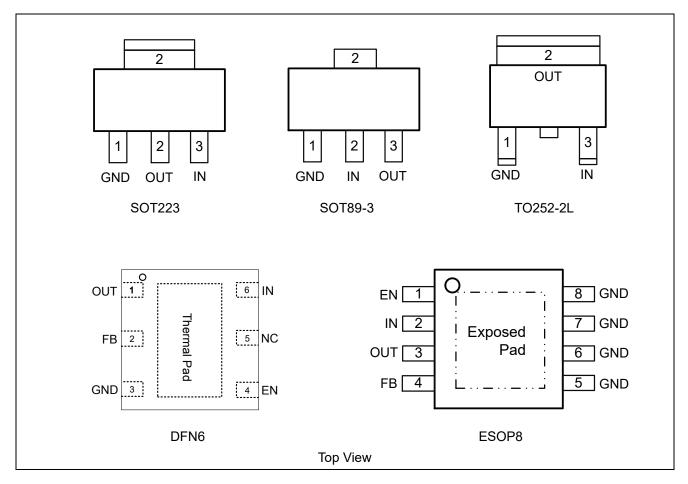
HM6118 <u>B</u> - <u>ADJ / XX</u> <u>X</u>

ADJ / XX Output Voltage	<u>X</u> Package		<u>B</u> Auto-Discharging Func
	Р	SOT89-3	
ADJ - Output Adjustable	Т	TO252-2L	B - Available
	R	SOT223	
XX - Output X.XV	E	ESOP8	/ - Not equipped
	D	DFN6	

Ordering Information

Vout	Package	Part No.	Description
ADJ	DFN6	HM6118B-ADJD	1A, Adjustable,Enable
ADJ	ESOP8	HM6118B-ADJE	1A, Adjustable,Enable
	SOT223	HM6118B-18R	1A
1.8V	SOT89-3	HM6118B-18P	1A
	TO252-2L	HM6118B-18T	1A
	SOT223	HM6118B-25R	1A
2.5V	SOT89-3	HM6118B-25P	1A
	TO252-2L	HM6118B-25T	1A
	SOT223	HM6118B-33R	1A
3.3V	SOT89-3	HM6118B-33P	1A
	TO252-2L	HM6118B-33T	1A
	SOT223	HM6118B-50R	1A
5.0V	SOT89-3	HM6118B-50P	1A
	TO252-2L	HM6118B-50T	1A

Pin Configuration



Pin Function

ET5HAXX

Pin Number			Pin Name	Functions
SOT223	SOT89-3	TO252-2L	FIII Name	Functions
1	1	1	GND	Ground
2	3	2	OUT	Output
3	2	3	IN	Power Supply Input

DFN6

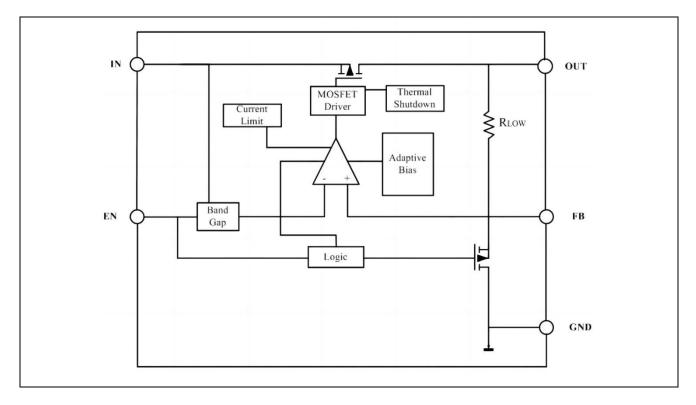
Pin Number	Pin Name	Functions	
1	OUT	Output	
2	FB	Set the output voltage of the LDO.	
3	GND	Ground	
4	EN	Enable Pin	
5	NC	Not Connect	
6	IN	Power Supply Input	

ESOP8

Pin Number	Pin Name	Functions	
1	EN	Enable Pin.	
2	VIN	Power Supply Input.	
3	OUT	Output.	
4	FB	Set the output voltage of the LDO.	
5	GND	Ground.	
6	GND	Ground.	
7	GND	Ground.	
8	GND	Ground.	



Block Diagram



Functional Description

Enable

The HM6118B delivers the output power when it is set to enable state. When it works in disable state, there is no output power and the operation quiescent current is almost zero. The enable pin (EN) is active high.

Shutdown

Turn off the device by forcing the EN pin to drop below $V_{EN(LO)}$. If shutdown capability is not required, connect EN to IN. The HM6118B has an internal pull down MOSFET that connects an $R_{PULLDOWN}$ resistor to ground when the device is disabled. The discharge time after disabling depends on the output capacitance (C_{OUT}) and the load resistance(R_L) in parallel with the pull-down resistor (R_{PD}).

Formula 1 calculates the time constant:

$$T = (R_{PD} \times R_L) / (R_{PD} + R_L)$$

(1)

Over-Temperature Protection

The over-temperature protection function will turn off the P-MOSFET when the junction temperature exceeds 150°C (typ.). Once the junction temperature cools down by approximately 20°C, the regulator will automatically resume operation.

Current-Limit Protection

The HM6118B provides current limit function to prevent the device from damages during over-load or shorted-circuit condition. This current is detected by an internal sensing transistor.



Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
Vin	Input Voltage ⁽¹⁾	0~24	V
Vout	Output Voltage	0.8~6	V
VCE	Chip Enable Input	-0.3~22	V
TJ _(MAX)	Maximum Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C
ESDнвм	Human Body Model ⁽²⁾	2000	V
ESDCDM	ESD Capability ⁽²⁾	1500	V
Latch up	Current Maximum Rating ⁽²⁾	200	mA

Stresses exceeding those listed in this table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

Note2. This device series incorporates ESD protection and is tested by the following methods:

ESD Human Body Model tested per EIA/JESD22-A114.

CDM tested per JESD22-C101 ; Latch up Current Maximum Rating tested per JEDEC78.

Thermal Characteristics

Symbol	Package	Ratings	Value	Unit
	MSOP8		150	°C/W
	DFN6	Thermal Characteristics,	100	°C/W
$R_{ extsf{ heta}JA}$	SOT223	Thermal Resistance,	110	°C/W
	SOT89-3	Junction-to-Air	125	°C/W
	TO252-2L		60	°C/W

Recommended Operating Conditions

Symbol	Parameter	Min	Unit
V _{IN}	Input Voltage	2.7 to 22	V
Ι _{ουτ}	Output Current	0 to 1	А
Та	Operating Ambient Temperature	-40 to 85	°C
CIN	Effective Input Ceramic Capacitor Value ⁽³⁾	1 to 10	uF
Соит	Effective Output Ceramic Capacitor Value ⁽³⁾	1 to 10	uF
ESR	Input and Output Capacitor Equivalent Series	nput and Output Capacitor Equivalent Series	
ESK	Resistance (ESR)	5 to 100	mΩ

Note3. The capacitor refers to a chip capacitor, and larger capacitance value is required if electrolytic capacitor is used.

Electrical Characteristics

$V_{IN} = V_{OUT} + 1V$; $I_{OUT} = 10$ mA, $C_{IN} = C_{OUT} = 10 \mu$ F, unless otherwise noted. Typical values are at $T_A = +25^{\circ}$	$V_{IN} = V_{OUT} + 1V; I_{OUT} = 2$	$0mA, C_{IN} = C_{OUT} = 1$	0µF, unless otherwise noted.	Typical values are at T _A = +25°C
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Symbol	Parameter	Test Conditions	Min	Тур.	Мах	Unit
V _{IN} ⁽⁴⁾	Operating Input Voltage		2.7		20	V
V	Quitaut \/oltogo	T _A = +25°C	-2%		+2%	V
V _{OUT}	Output Voltage	-40°C ≤ T _A ≤ 85°C	-3%		+3%	
VREF	Reference Voltage	T _A = +25°C	0.588	0.60	0.612	V
Line _{Reg}	Line Regulation	$2.8V \le V_{IN} \le 20V,$ $I_{OUT} = 10mA$		0.05	0.20	%/V
	Dropout Voltage	V _{OUT} =1.8 V		750	800	
	I _{OUT} =1A,V _{IN} ≥2.7V	V _{OUT} =3.3V		480	600	mV
VDROP	-40°C ≤ T _A ≤ 125°C	Vout=5.0V		450	550	
(5)	Dropout Voltage	Vout=1.8 V		650	900	
	I _{0UT} =500mA,V _{IN} ≥2.7V	V _{OUT} =3.3V		210	450	mV
	-40°C ≤ T _A ≤ 125°C	Vout=5.0V		200	400	
Load _{Reg}	Load Regulation	$1mA \le I_{OUT} \le 800mA$, $V_{IN} = V_{OUT} + 1V$			40	mV
ILMT	Current Limit	VIN =VOUT+1V	1.04	1.3		A
ISHORT	Short Circuit Current Limit	V _{OUT} = 0V		330		mA
la	Quiescent Current	Ι _{ΟυΤ} = 0mA		160	190	μA
I_{Q_OFF}	Standby Current	V _{EN} = 0V, T _A = 25°C		0.1	1	μA
Venh	EN Pin Threshold Voltage	EN Input Voltage "H"	1.4			V
VENL	EN Pin Threshold Voltage	EN Input Voltage "L"			0.4	V
I _{EN}	EN Pin Current	$V_{EN} \le V_{IN} \le 20V$		1		uA
	Power Supply Rejection Ratio	f = 1 kHz		80		
PSRR	V _{IN} =V _{OUT} +2V	f = 100 kHz		70		dB
	Ι _{ΟUT} = 50mA	f = 1 MHz		65		
en	Output Noise Voltage	$V_{IN} = V_{OUT}+1V$, $I_{OUT} = 1mA$, f = 10Hz to 100KHz, $V_{OUT}=3V$, $C_{OUT} = 1\mu F$ ⁽⁴⁾ ⁽⁵⁾		30* V _{оит}		μVrms
RLOW	Active Output Discharge Resistance	$V_{IN} = 4V, V_{EN} = 0V$		300		Ω
T _{SD}	Thermal Shut down Temperature	Temperature Increasing from T_A =+25°C ⁽⁶⁾		150		C
TSDH	Thermal Shutdown Hysteresis	Temperature Falling from T _{SD} (6)		25		C

Note4. V_{IN} range guarantees internal circuit can work normal.

If VIN<VOUTSET, VOUT follows VIN(IOUT=1mA), circuit is safe still.

Note5. The minimum operating voltage is 2.7V. $V_{DROP}=V_{IN(min)}-V_{OUT}$.

V_{DROP} FT test method: Test the V_{OUT} voltage at V_{OUTSET} + V_{DROP-MAX} with 1A output current.

Note6. Guaranteed by design, not an FT item.

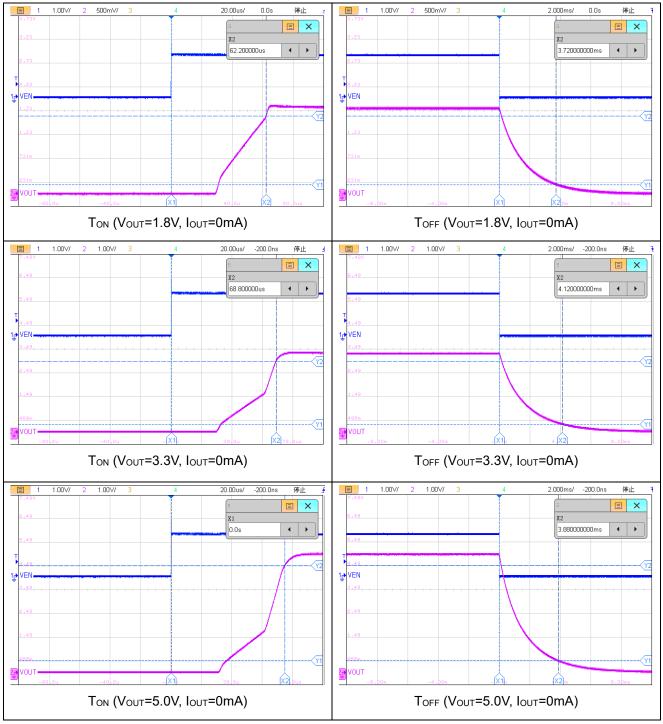


Typical Characteristics

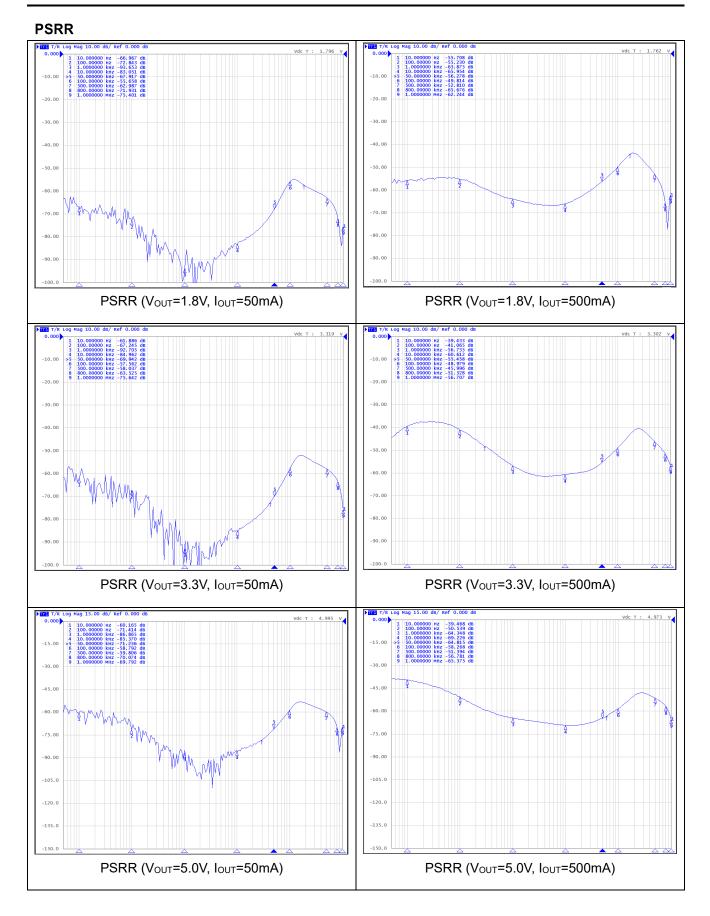
Typical Characteristics are ONLY for reference, thus they are not guaranteed.in practical use.

 $V_{IN} = V_{OUT} + 1V$, $I_{OUT} = 1mA$, $C_{IN} = C_{OUT} = 10\mu F$ (Ceramic Cap), unless otherwise noted.

TON and TOFF



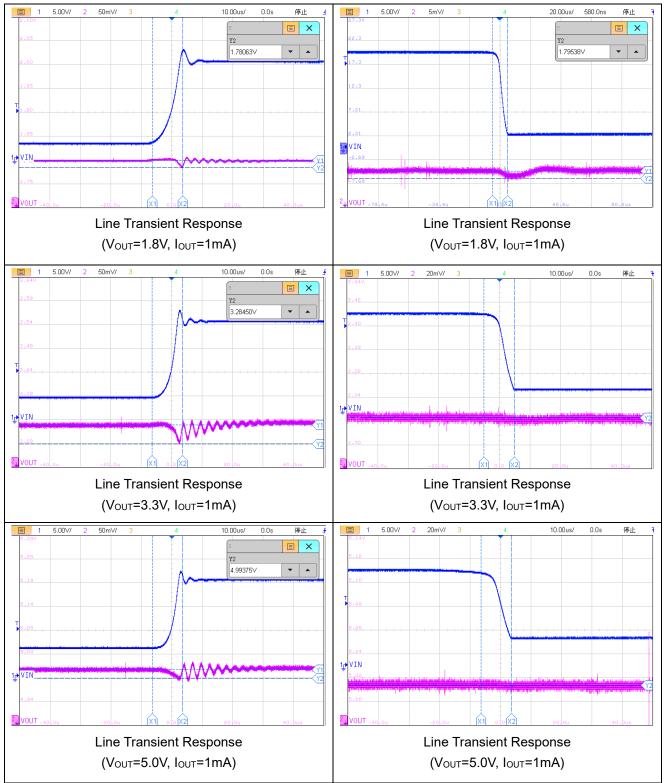






Line Transient Response

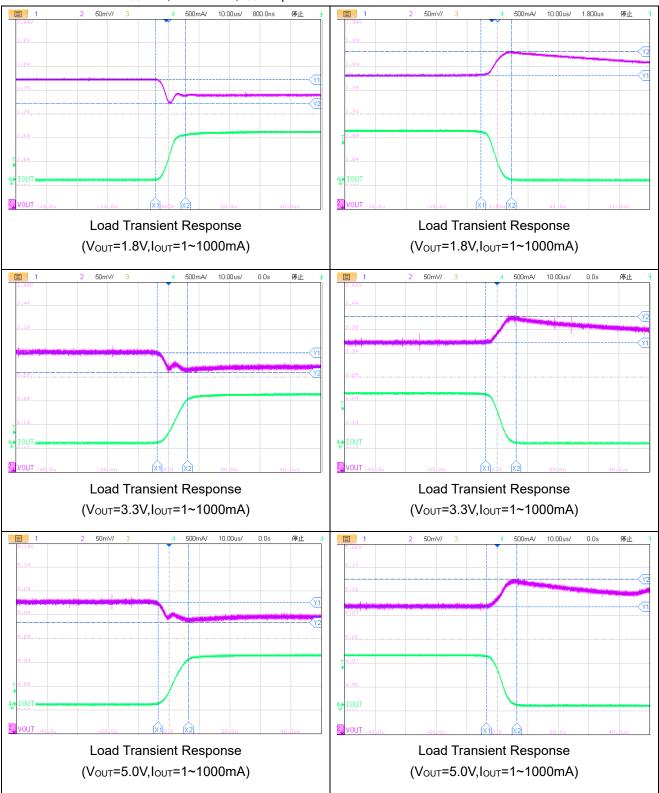
Test Condition: $V_{IN}=V_{OUT}+1V$, $C_{OUT}=10\mu$ F, $t_R=T_F=10us$, $I_{OUT}=10mA$, V_{IN} step between $6V \sim 18V$.





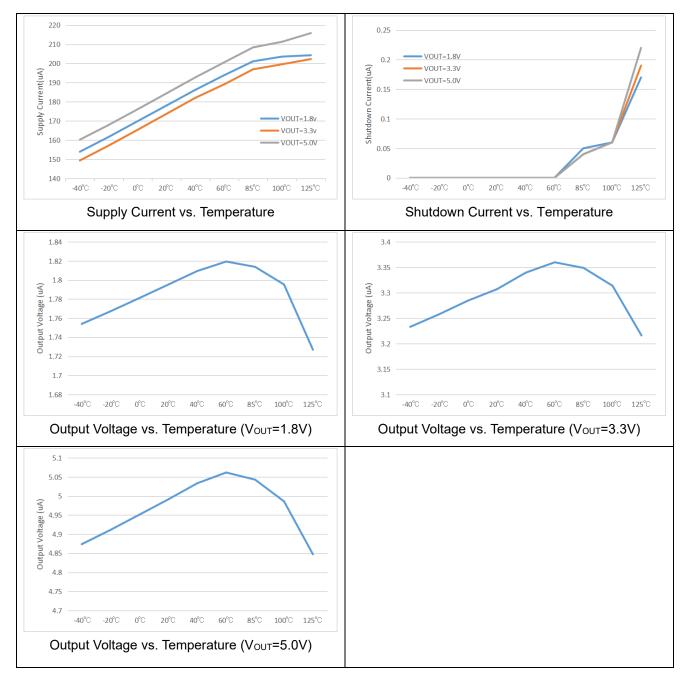
Load Transient Response

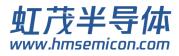
Test Condition: $V_{IN}=V_{OUT}+1V$, $t_R=T_F=10us$, I_{OUT} step between $1mA \sim 1000mA$.



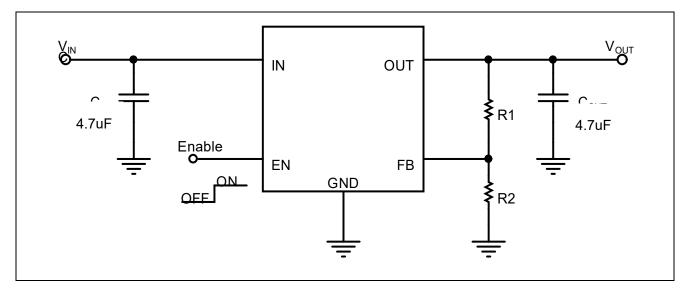


Temperature Characteristics





Application Circuits



Application Information

Input and Output Capacitor Selection

The HM6118B requires an output capacitance of 4.7µF or larger for stability. Use X5R and X7R type ceramic capacitors because these capacitors have minimal variation in value and equivalent series resistance (ESR) over temperature. When choosing a capacitor for a specific application, pay attention to the dc bias characteristics for the capacitor. Higher output voltages cause a significant derating of the capacitor.

Although an input capacitor is not required for stability, good analog design practice is to connect a capacitor from IN to GND. Some input supplies have a high impedance, thus placing the input capacitor on the input supply helps reduce the input impedance. This capacitor counteracts reactive input sources and improve stransient response, input ripple, and PSRR. If the input supply has a high impedance over a large range off requencies, several input capacitors can be used in parallel to lower the impedance over frequency. Use a higher-value capacitor if large, fast, rise-time load transients are anticipated, or if the device is located several inches from the input power source.

Application of Electrolytic Capacitor

If the electrolytic capacitor should be used as input and output capacitor, the capacitance of the capacitor must be greater. The capacity value must be greater than 22uF.

Enable

The HM6118B has an EN pin to turn on or turn off the regulator, When the EN pin is in logic high, the regulator will be turned on. The shutdown current is almost 0uA typical. The EN pin may be directly tied to V_{IN} to keep the part on. The Enable input is CMOS logic and cannot be left floating.

Setting the Output Voltage

The HM6118B develops a 0.6V reference voltage, V_{REF} , between the output and the adjust terminal. This voltage is applied across resistor R1 to generate a constant current. The current I_{ADJ} from the ADJ terminal could introduce DC offset to the output. Because, this offset is very small (about 0.1 uA), it can be ignored.

The constant current then flows through the output set resistor R2 and sets the output voltage to the desired

level. Formula 2 is used for calculating V_{OUT} :

V_{OUT} = 0.6V × (1 + R1 / R2)

Although I_{ADJ} is very small, R1+R2 should be limited to less than 100 K Ω for optimum performance.

Dropout Voltage

The HM6118B uses a PMOS pass transistor to achieve low dropout. When $(V_{IN} - V_{OUT})$ is less than the dropout voltage (V_{DO}) , the PMOS pass device is in the linear region of operation and the input-to-output resistance is the $R_{DS(ON)}$ of the PMOS pass element. V_{DO} scales approximately with output current because the PMOS device behaves like a resistor in dropout mode. As with any linear regulator, PSRR and transient response degrade as ($V_{IN} - V_{OUT}$) approaches dropout operation.

Thermal Shutdown

Thermal shutdown protection disables the output when the junction temperature rises to approximately 150° C.Disabling the device eliminates the power dissipated by the device, allowing the device to cool. When the junction temperature cools to approximately 125° C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits regulator dissipation, protecting the LDO from damage as a result of overheating. Activating the thermal shutdown feature usually indicates excessive power dissipation as a result of the product of the (V_{IN} - V_{OUT}) voltage and the load current. For reliable operation, limit junction temperature to 150°C maximum.

Thermal Considerations

For continuous operation, do not exceed absolute maximum junction temperature. The maximum power dissipation depends on the thermal resistance of the IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated by Formula 3:

$PD_{(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$

(3)

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction to ambient thermal resistance.

For recommended operating condition specifications the maximum junction temperature is 150°C and T_A is the ambient temperature. The junction to ambient thermal resistance, θ_{JA} , is layout dependent. For DFN6 package, the thermal resistance, θ_{JA} , is 100°C/W on the test board. The maximum power dissipation at T_A = 25°C can be calculated by Formula 4:

$$PD_{(MAX)} = (150^{\circ}C - 25^{\circ}C) / (100^{\circ}C/W) = 1.25W$$

(2)

(4)



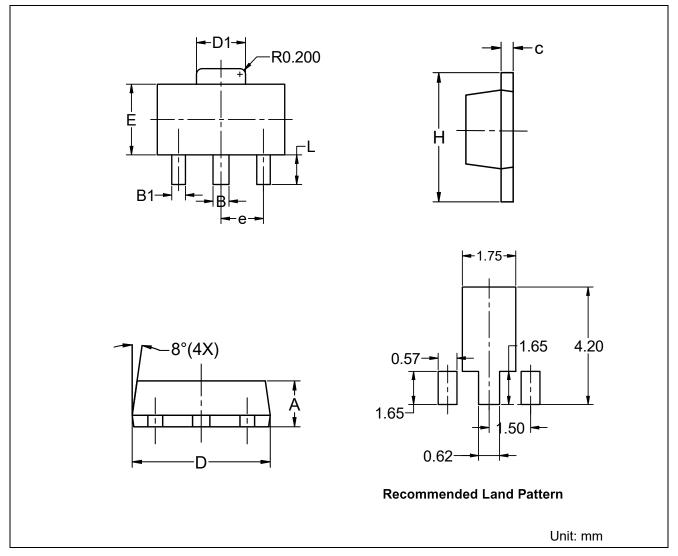
Layout

Layout Guidelines

- Place input and output capacitors as close to the device as possible.
- Use copper planes for device connections in order to optimize thermal performance.
- Place thermal vias around the device to distribute heat.
- Do not place a thermal via directly beneath the thermal pad of the DRV package. A via can wick solder or solder paste away from the thermal pad joint during the soldering process, leading to a compromised solder joint on the thermal pad.

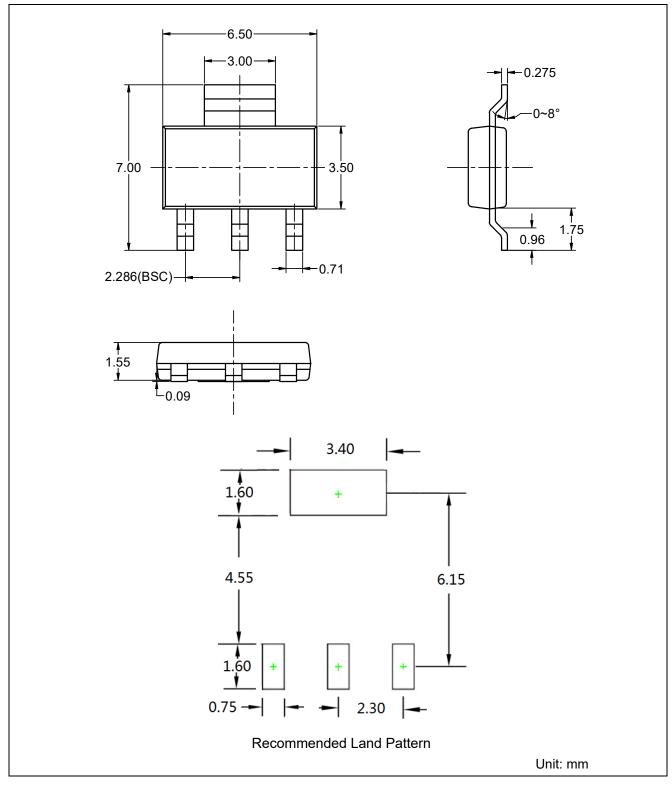
Package Dimension

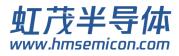
SOT89-3



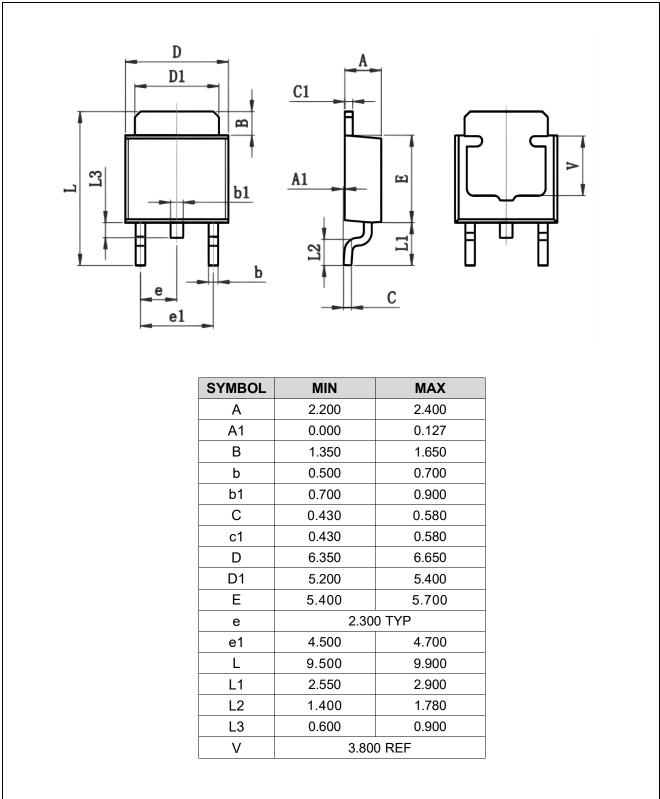


SOT-223



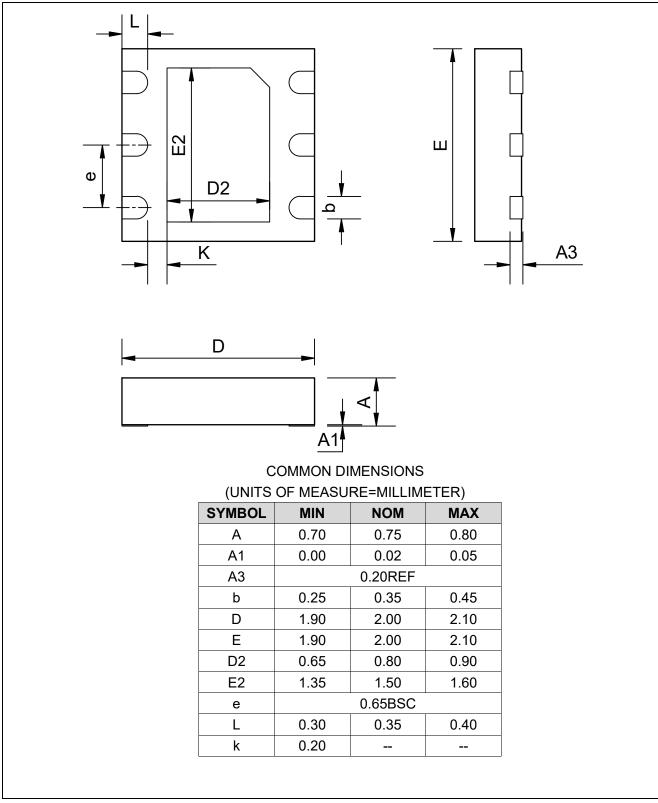


TO252-2





DFN6 (2×2)





ESOP-8

